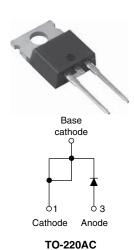


### Vishay Semiconductors

# HEXFRED® Ultrafast Soft Recovery Diode, 25 A



PRODUCT SUMMARY						
Package	TO-220AC					
I <sub>F(AV)</sub>	25 A					
V <sub>R</sub>	600 V					
V <sub>F</sub> at I <sub>F</sub>	1.7 V					
t <sub>rr</sub> (typ.)	23 ns					
T <sub>J</sub> max.	150 °C					
Diode variation	Single die					

### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level





### **BENEFITS**

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA25TB60PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the VS-HFA25TB60PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA25TB60PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V <sub>R</sub>		600	V		
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	25			
Single pulse forward current	I <sub>FSM</sub>		225	Α		
Maximum repetitive forward current	I <sub>FRM</sub>		100			
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	125	W		
Maximum power dissipation		T <sub>C</sub> = 100 °C	50	VV		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C		

## VS-HFA25TB60PbF

# Vishay Semiconductors

## **HEXFRED®** Ultrafast Soft Recovery Diode, 25 A



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA		600	-	-	
		I <sub>F</sub> = 25 A		-	1.3	1.7	V
Maximum forward voltage	$V_{FM}$	$V_{FM}$ $I_F = 50 A$ See fig. 1	-	1.5	2.0		
		I <sub>F</sub> = 25 A, T <sub>J</sub> = 125 °C		-	1.3	1.7	
Maximum reverse		V <sub>R</sub> = V <sub>R</sub> rated	See fig. 2	-	1.5	20	
leakage current	I <sub>RM</sub>	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See lig. 2	-	600	2000	μA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	-	55	100	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body		-	8.0	-	nH

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	0 A/μs, V <sub>R</sub> = 30 V	-	23	-		
Reverse recovery time See fig. 5, 6 and 16	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	50	75	ns	
occ lig. 5, 5 and 15	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	105	160		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 25 A	-	4.5	10	А	
See fig. 7 and 8	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	8.0	15		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	dl <sub>F</sub> /dt = 200 A/µs	-	112	375	nC	
See fig. 9 and 10	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C	V <sub>R</sub> = 200 V	-	420	1200	IIC	
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 11 and 12	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	250	-	A/µs	
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	160	-	AνμS	

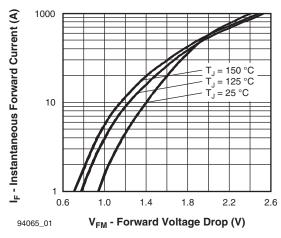
THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	1.0			
Thermal resistance, junction to ambient	R <sub>thJA</sub>	hJA Typical socket mount		-	80	K/W		
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-			
Weight			-	2.0	-	g		
vveignt			-	0.07	-	OZ.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-220AC	HFA25TB60			•		





## HEXFRED® Ultrafast Soft Recovery Diode, 25 A

## Vishay Semiconductors



10 000 T<sub>J</sub> = 150 °C 1000 I<sub>R</sub> - Reverse Current (µA) T<sub>1</sub> = 125 °C 100 10 T<sub>J</sub> = 25 °C 0.1 0.01 0 100 200 300 400 500 600 94065\_02 V<sub>R</sub> - Reverse Voltage (V)

Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

Fig. 2 - Typical Reverse Current vs. Reverse Voltage

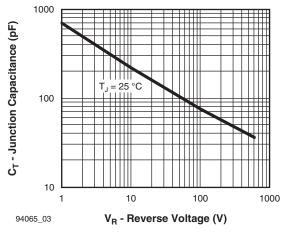


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

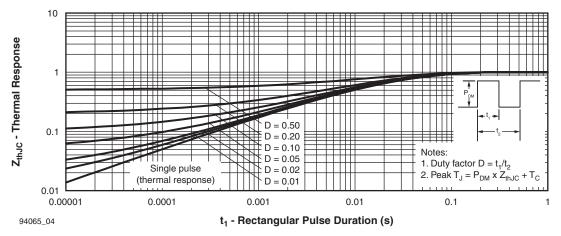


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

# Vishay Semiconductors

## HEXFRED® Ultrafast Soft Recovery Diode, 25 A



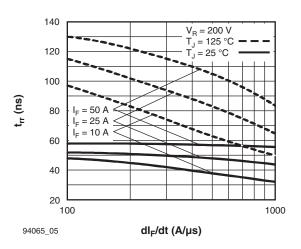


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

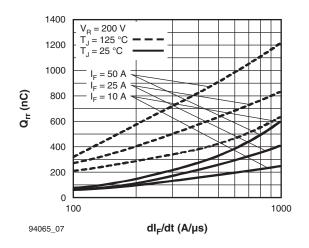


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

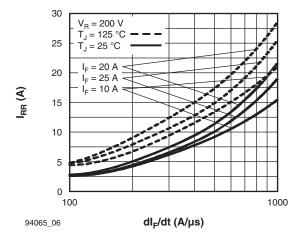


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

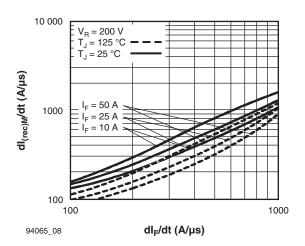


Fig. 8 - Typical dI<sub>(rec)M</sub>/dt vs. dI<sub>F</sub>/dt



# HEXFRED® Ultrafast Soft Recovery Diode, 25 A

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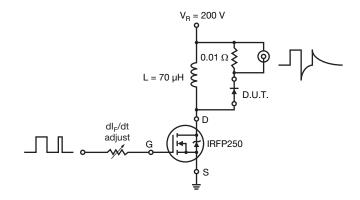
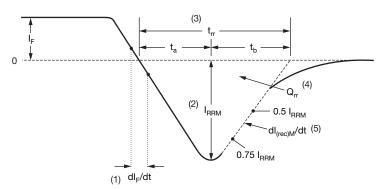


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm l_F$  to point where a line passing through 0.75  $\rm l_{RRM}$  and 0.50  $\rm l_{RRM}$  extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions

### VS-HFA25TB60PbF

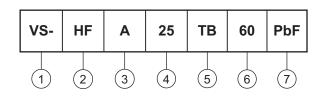
## Vishay Semiconductors

# HEXFRED® Ultrafast Soft Recovery Diode, 25 A



### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

Current rating (25 = 25 A)

5 - Package:

TB = TO-220AC

6 - Voltage rating (60 = 600 V)

7 - PbF = Lead (Pb)-free

Tube standard pack quantity: 50 pieces

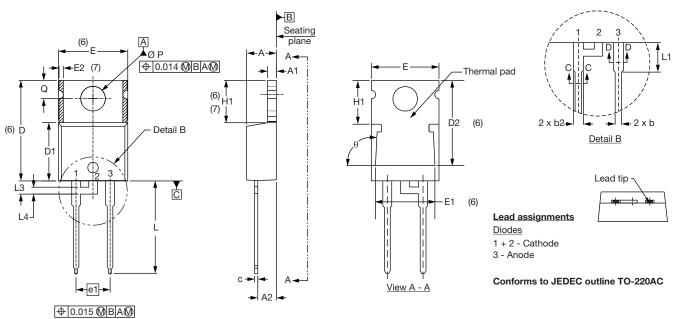
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95221</u>					
Part marking information	www.vishay.com/doc?95224				



### Vishay Semiconductors

### **TO-220AC**

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	IETERS	INCHES		NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIMETERS		INCHES		INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		
E1	6.86	8.89	0.270	0.350	6		
E2	-	0.76	-	0.030	7		
е	2.41	2.67	0.095	0.105			
e1	4.88	5.28	0.192	0.208			
H1	6.09	6.48	0.240	0.255	6, 7		
L	13.52	14.02	0.532	0.552			
L1	3.32	3.82	0.131	0.150	2		
L3	1.78	2.13	0.070	0.084			
L4	0.76	1.27	0.030	0.050	2		
ØΡ	3.54	3.73	0.139	0.147			
Q	2.60	3.00	0.102	0.118			
θ	90° t	o 93°	90° to 93°				

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline





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